



**METHOD FOR PROGRAMMING A THREE-DIMENSIONAL MEMORY  
ARRAY INCORPORATING SERIAL CHAIN DIODE STACK**

Bendik Kleveland  
Roy E. Scheuerlein

*C. yeh  
7104*

**CROSS-REFERENCE TO RELATED APPLICATIONS**

[1001] This application is a divisional of Prior Application No. 10/253,074 filed September 24, 2002, which is a divisional of Application No. 09/897,705, filed June 29, 2001, which is a continuation-in-part of U.S. Application No. 09/814,727, filed March 21, 2001, which is a continuation-in-part of U.S. Application No. 09/560,626, filed April 28, 2000; each of which applications is hereby incorporated by reference; and which Application No. 09/897,705, also claims the benefit of the following U.S. provisional applications: U.S. Provisional Application No. 60/277,794 filed on March 21, 2001; U.S. Provisional Application No. 60/277,815 filed on March 21, 2001; and U.S. Provisional Application No. 60/277,738 filed on March 21, 2001; each of which provisional applications is also hereby incorporated by reference.

*Now a patent 6,754,102,  
Now a patent 6,631,085,  
Now a patent 6,420,215,  
now abandoned,  
now a patent 6,631,085*

**BACKGROUND OF THE INVENTION**

**Field of the Invention**

[1002] The present invention relates to low cost, high-density semiconductor memories and, in particular, to one-time-programmable semiconductor memories. More particularly, the invention relates to the field of vertically stacked field programmable non-volatile memory, support circuits useful therewith, and methods of fabrication thereof.